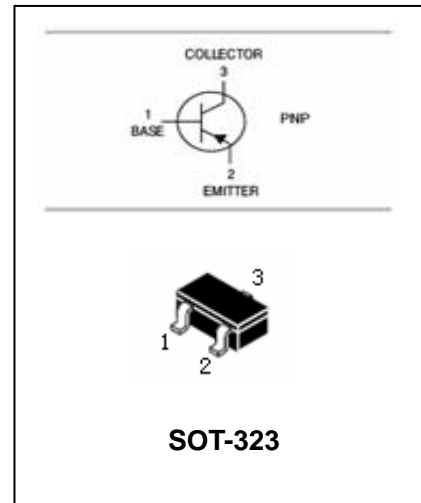


PNP Silicon Epitaxial Planar Transistor

2SA1579W

FEATURES

- Power dissipation.($P_C=200\text{mW}$)
- Excellent H_{FE} Linearity.



APPLICATIONS

- General purpose application.

ORDERING INFORMATION

Type No.	Marking	Package Code
2SA1579W	HP/HQ/HR	SOT-323

MAXIMUM RATING @ $T_a=25^\circ\text{C}$ unless otherwise specified

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	-120	V
V_{CEO}	Collector-Emitter Voltage	-120	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current -Continuous	-50	mA
P_C	Collector Dissipation	200	mW
T_j, T_{stg}	Junction and Storage Temperature	-55~150	$^\circ\text{C}$

PNP Silicon Epitaxial Planar Transistor**2SA1579W****ELECTRICAL CHARACTERISTICS @ Ta=25°C unless otherwise specified**

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=-50\mu A, I_E=0$	-120			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=-1mA, I_B=0$	-120			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=-50\mu A, I_C=0$	-5			V
Collector cut-off current	I_{CBO}	$V_{CB}=-100V, I_E=0$			-0.5	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=-4V, I_C=0$			-0.5	μA
DC current gain	h_{FE}	$V_{CE}=-6V, I_C=-2mA$	180		560	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=-10mA, I_B=-1mA$			-0.5	V
Transition frequency	f_T	$V_{CE}=-12V, I_C=-2mA$ $f=30MHz$		140		MHz
Collector output capacitance	C_{ob}	$V_{CB}=-12V, I_E=0, f=1MHz$		3.2		pF

CLASSIFICATION OF h_{FE}

Rank	S	R
Range	180-390	270-560
marking	RR	RS

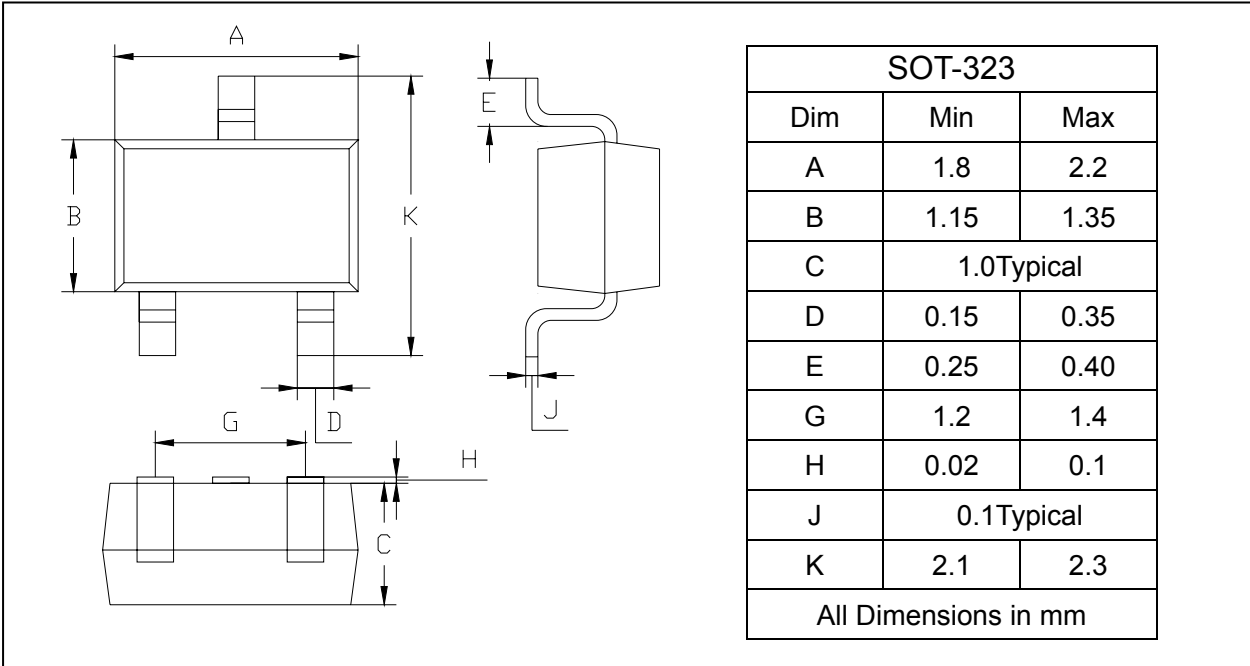
PNP Silicon Epitaxial Planar Transistor

2SA1579W

PACKAGE OUTLINE

Plastic surface mounted package

SOT-323



PACKAGE INFORMATION

Device	Package	Shipping
2SA1579W	SOT-323	3000/Tape&Reel